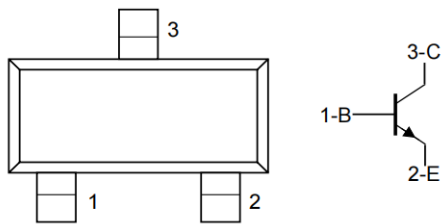


SOT-323


PIN1:Base PIN2:Emitter PIN3:Collector

Features

- Epitaxial Planar Die Construction
- Complementary PNP Type Available (MMBT5401W)
- Ideal for Low Power Amplification and Switching
- Marking Code:K4N

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	180	V
Collector Emitter Voltage	V_{CEO}	160	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	600	mA
Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_{amb}=25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain				
at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	h_{FE}	80	-	-
at $V_{CE} = 5\text{ V}$, $I_C = 10\text{ mA}$	h_{FE}	80	250	-
at $V_{CE} = 5\text{ V}$, $I_C = 50\text{ mA}$	h_{FE}	30	-	-
Collector Base Cutoff Current at $V_{CB} = 120\text{ V}$	I_{CBO}	-	50	nA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	50	nA
Collector Base Breakdown Voltage at $I_C = 100\text{ }\mu\text{A}$	$V_{(BR)CBO}$	180	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	160	-	V
Emitter Base Breakdown Voltage at $I_E = 10\text{ }\mu\text{A}$	$V_{(BR)EBO}$	6	-	V
Collector Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{CE(sat)}$	- -	0.15 0.2	V
Base Emitter Saturation Voltage at $I_C = 10\text{ mA}$, $I_B = 1\text{ mA}$ at $I_C = 50\text{ mA}$, $I_B = 5\text{ mA}$	$V_{BE(sat)}$	- -	1 1	V
Gain Bandwidth Product at $V_{CE} = 10\text{ V}$, $I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	300	MHz
Collector Base Capacitance at $V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{cbo}	-	6	pF

Typical Characteristics

Fig. 1 Output Characteristics Curve

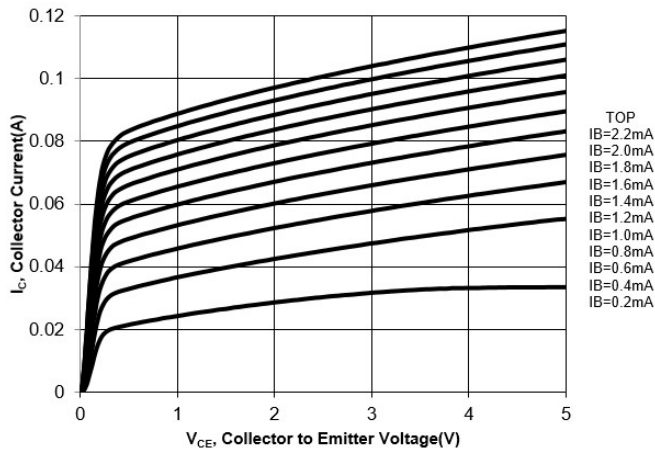


Fig. 2 Output Characteristics Curve

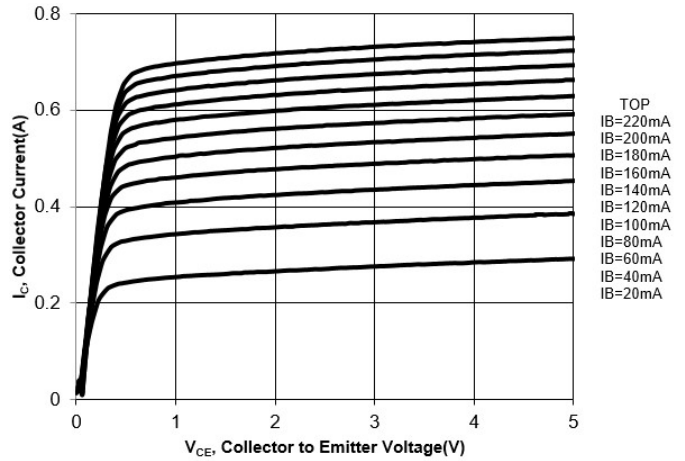


Fig. 3 DC Current Gain vs. Collector Current

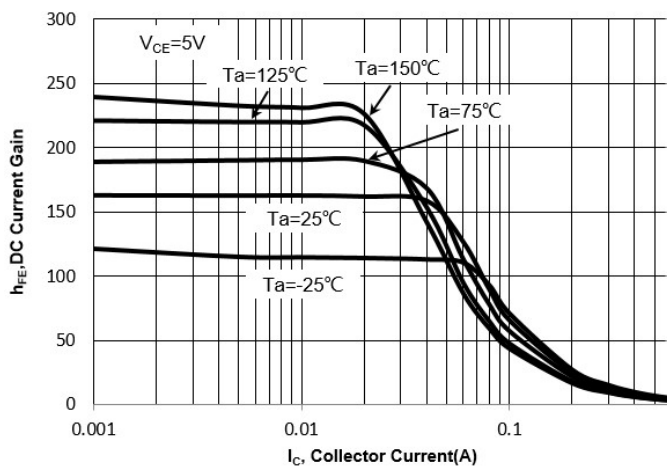


Fig. 4 Collector Current vs. Base to Emitter Voltage

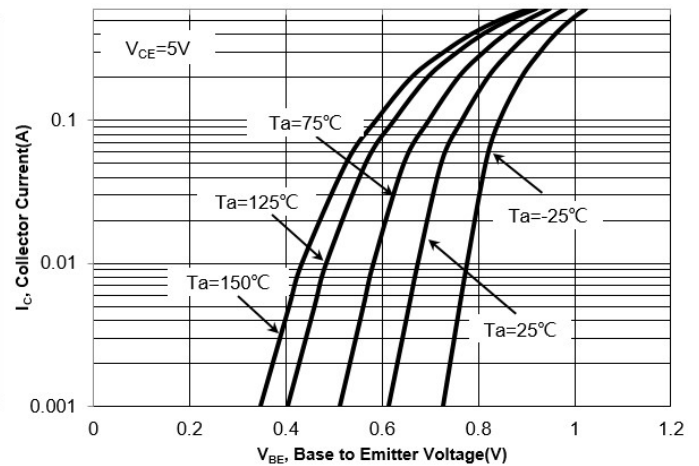


Fig. 5 V_{BESAT} vs. Collector Current

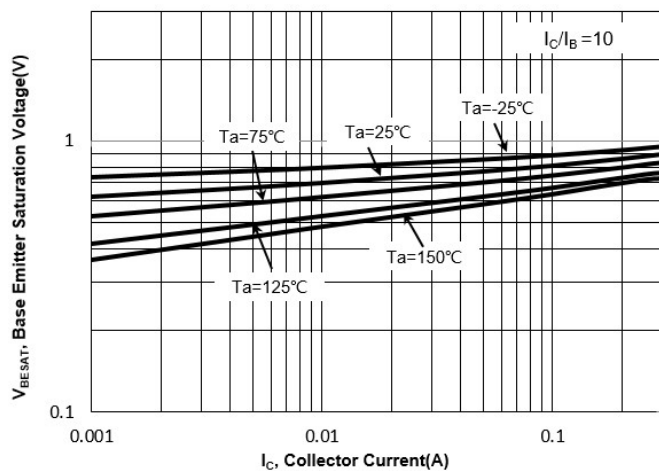
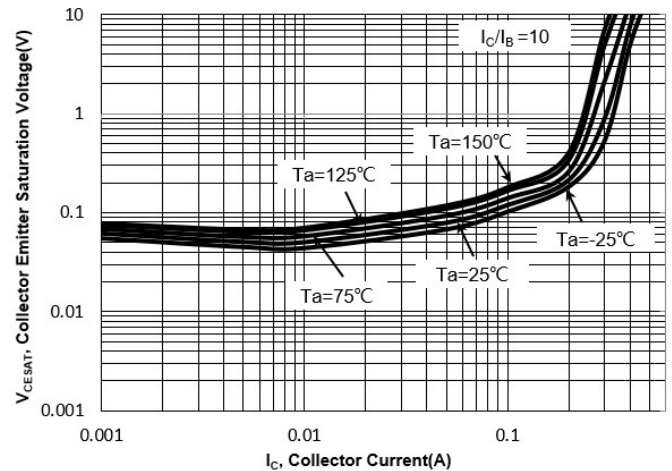
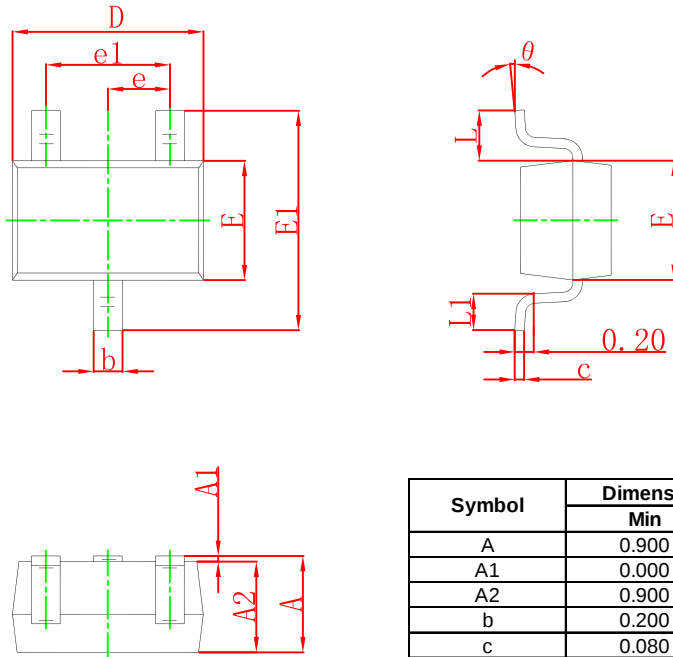


Fig. 6 V_{CESAT} vs. Collector Current

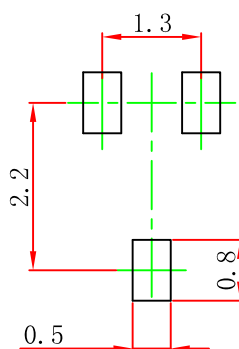


SOT-323 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP		0.026 TYP	
e1	1.200	1.400	0.047	0.055
L	0.525 REF		0.021 REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

SOT-323 Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$.
3. The pad layout is for reference purposes only.